

L Number	Hits	Search Text	DB	Time stamp
3	4	("4336489").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/06 10:34
-	0	("salicide").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/05 17:00
-	2475	salicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/05 17:08
-	431	salicide.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/05 17:08
-	229	(257/173).CCLS.	USPAT; US-PGPUB	2002/10/04 11:04
-	322	(257/339).CCLS.	USPAT; US-PGPUB	2002/10/04 11:04
-	725	(257/355).CCLS.	USPAT; US-PGPUB	2002/10/04 11:04
-	1186	((257/173).CCLS.) or ((257/339).CCLS.) or ((257/355).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 12:05
-	18	(((257/173).CCLS.) or ((257/339).CCLS.) or ((257/355).CCLS.)) and (mos or mosfet or nmos or nmosfet or pmos or pmosfet or cmos or cmosfet) and protect\$3 and silicide and zener	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 13:58
-	18	(US-6307238-\$ or US-6281527-\$ or US-6268639-\$ or US-6175139-\$ or US-6121665-\$ or US-5939767-\$ or US-5910675-\$ or US-5708288-\$ or US-5683918-\$ or US-5623387-\$ or US-5543650-\$ or US-5229633-\$ or US-5166089-\$ or US-5128730-\$ or US-4509089-\$ or US-6365941-\$).did. or (US-20020096722-\$ or US-20020030231-\$).did.	USPAT; US-PGPUB	2002/10/04 13:29
-	132	(((257/173).CCLS.) or ((257/339).CCLS.) or ((257/355).CCLS.)) and (mos or mosfet or nmos or nmosfet or pmos or pmosfet or cmos or cmosfet) and zener	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 14:07
-	30	((257/288).CCLS.) and second near3 diffusion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 14:16
-	7	((257/288).CCLS.) and double-diffused	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 14:17
-	11	((257/288).CCLS.) and double adj diffused	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 14:18

-	788	(257/288).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 14:31
-	8	(US-6025628-\$ or US-6307224-\$ or US-4509089-\$ or US-5166089-\$ or US-6268639-\$ or US-5623387-\$).did. or (US-20020030231-\$).did. or (JP-06204475-\$).did.	USPAT; US-PGPUB; JPO	2002/10/04 19:04
-	8	((US-6025628-\$ or US-6307224-\$ or US-4509089-\$ or US-5166089-\$ or US-6268639-\$ or US-5623387-\$).did. or (US-20020030231-\$).did. or (JP-06204475-\$).did.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 19:18
-	463	well same protect\$3 same substrate same esd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 19:19
-	268	well same protect\$3 same substrate same esd and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 19:19
-	112	(well same protect\$3 same substrate same esd and 257/\$6.ccls.) and well near4 protect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 19:20
-	37	(well same protect\$3 same substrate same esd and 257/\$6.ccls.) and well near4 protect\$3.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 19:21
-	12	(well same protect\$3 same substrate same esd and 257/\$6.ccls.) and well near4 protect\$3.ti,ab,clm. and (mos or mosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 19:22